

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor Rev. 01 — 31 March 2010

Product data sheet

Product profile 1.

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4021NZ.

1.2 Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-20	V
I _C	collector current		-	-	-6.6	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-	-20	A
R _{CEsat}	collector-emitter saturation resistance	l _C = -6 A; l _B = -600 mA	<u>[1]</u> _	22	33	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

nexperia

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline G	raphic symbol
1	base		
2	collector		2, 4
3	emitter		1
4	collector		3
			sym028

3. Ordering information

Table 3. Ordering information						
Type number	Package	ge				
	Name	Description	Version			
PBSS4021PZ	SC-73	plastic surface-mounted package with increased heat sink; 4 leads	SOT223			

4. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS4021PZ	PB4021PZ

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

			-		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-20	V
V _{CEO}	collector-emitter voltage	open base	-	-20	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current		-	-6.6	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 ms$	-	-20	A
I _B	base current		-	-1	А

PBSS4021PZ_1 Product data sheet

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

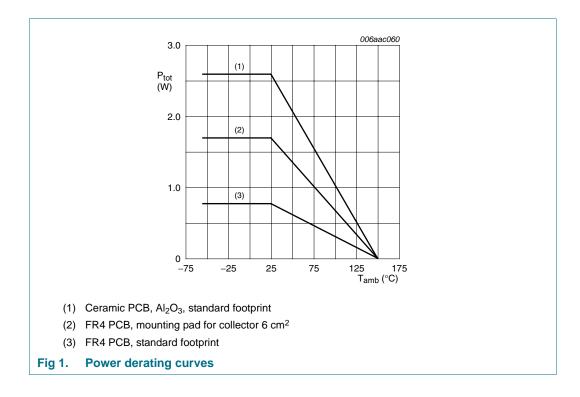
Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot} total power dissipat	total power dissipation	bation $T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	770	mW
			[2] _	1700	mW
			[3] _	2600	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
Г _{stq}	storage temperature		-65	+150	°C

 Table 5.
 Limiting values ...continued

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.



PBSS4021PZ_1 Product data sheet

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

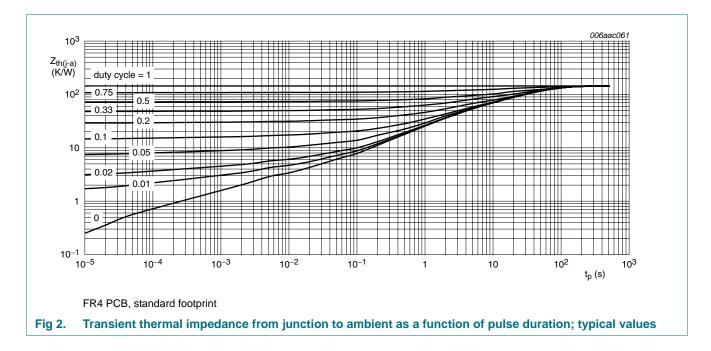
6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
uii(j-a)	thermal resistance from	in free air	<u>[1]</u> _	-	160	K/W
	junction to ambient		[2] _	-	75	K/W
			<u>[3]</u> _	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	11	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

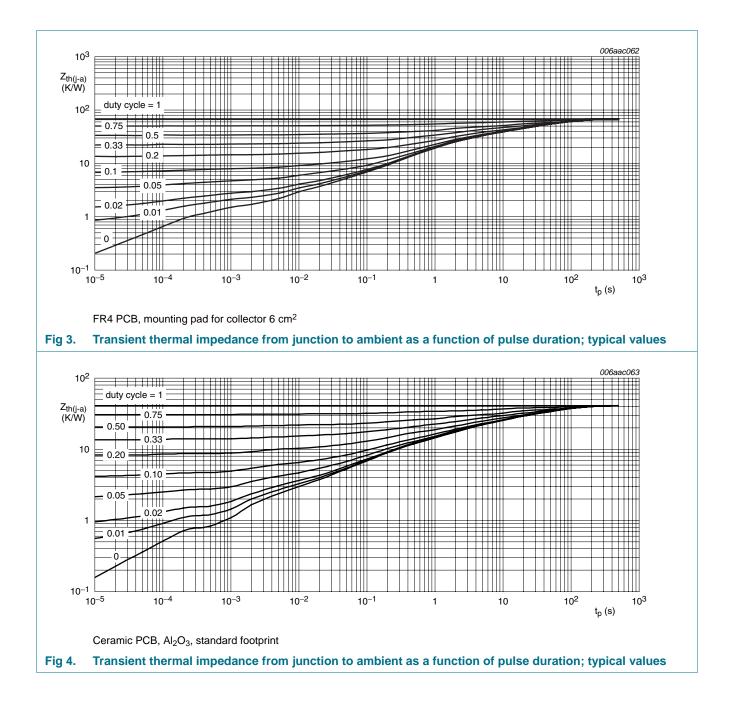
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.



PBSS4021PZ

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor



20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

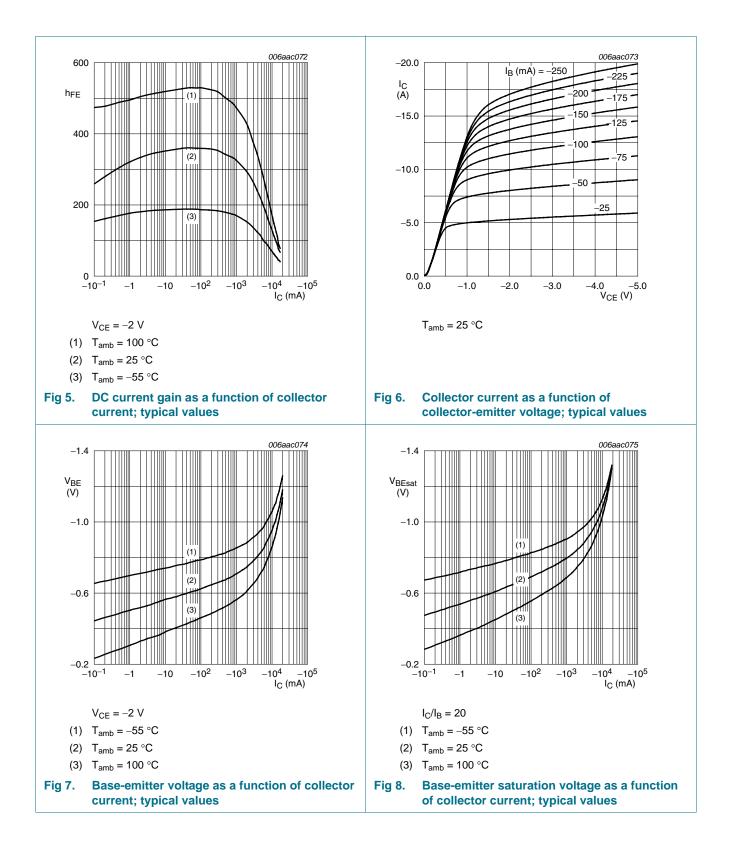
7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -20 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
	current	$\label{eq:VCB} \begin{array}{l} V_{CB} = -20 \text{ V}; \text{ I}_E = 0 \text{ A}; \\ T_j = 150 \ ^\circ\text{C} \end{array}$		-	-	-55	μA
I _{CES}	collector-emitter cut-off current	$V_{CE} = -16 \text{ V}; \text{ V}_{BE} = 0 \text{ V}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain		[1]				
		$V_{CE} = -2 V;$ $I_{C} = -500 \text{ mA}$		250	400	-	
		V_{CE} = -2 V; I_C = -1 A		250	400	-	
		$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -2 \text{ A}$		200	350	-	
		$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -4 \text{ A}$		150	250	-	
		$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -7 \text{ A}$		100	180	-	
V _{CEsat} collector-emitter			[1]				
	saturation voltage	$I_{C} = -1 \text{ A}; I_{B} = -50 \text{ mA}$		-	-31	-50	mV
		I_{C} = -1 A; I_{B} = -10 mA		-	-53	-80	mV
		$I_{C} = -2 \text{ A}; I_{B} = -40 \text{ mA}$		-	-66	-100	mV
		$I_{C} = -4 \text{ A}; I_{B} = -200 \text{ mA}$		-	-95	-140	mV
		$I_C = -4 \text{ A}; I_B = -40 \text{ mA}$		-	-150	-225	mV
		$I_{C} = -7$ A; $I_{B} = -350$ mA		-	-160	-240	mV
R _{CEsat}	collector-emitter saturation resistance	$I_{\rm C} = -6$ A; $I_{\rm B} = -600$ mA	<u>[1]</u>	-	22	33	mΩ
V _{BEsat}	base-emitter	$I_C = -1$ A; $I_B = -50$ mA	[1]	-	-0.79	-0.9	V
	saturation voltage	$I_{C} = -4 \text{ A}; I_{B} = -400 \text{ mA}$	[1]	-	-0.94	-1.05	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -2 \text{ A}$	[1]	-	-0.73	-0.85	V
t _d	delay time	$V_{CC} = -12.5 V;$		-	55	-	ns
t _r	rise time	$I_{C} = -1 \text{ A}; I_{Bon} = -0.05 \text{ A};$ $I_{Boff} = 0.05 \text{ A}$		-	60	-	ns
t _{on}	turn-on time	IROII - 0.00 V		-	115	-	ns
t _s	storage time			-	400	-	ns
t _f	fall time			-	110	-	ns
t _{off}	turn-off time			-	510	-	ns
f _T	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -100 \text{ mA};$ f = 100 MHz		-	85	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A}; \text{ f} = 1 \text{ MHz}$		-	125	-	pF

 $\label{eq:point} \begin{tabular}{ll} \begin{$

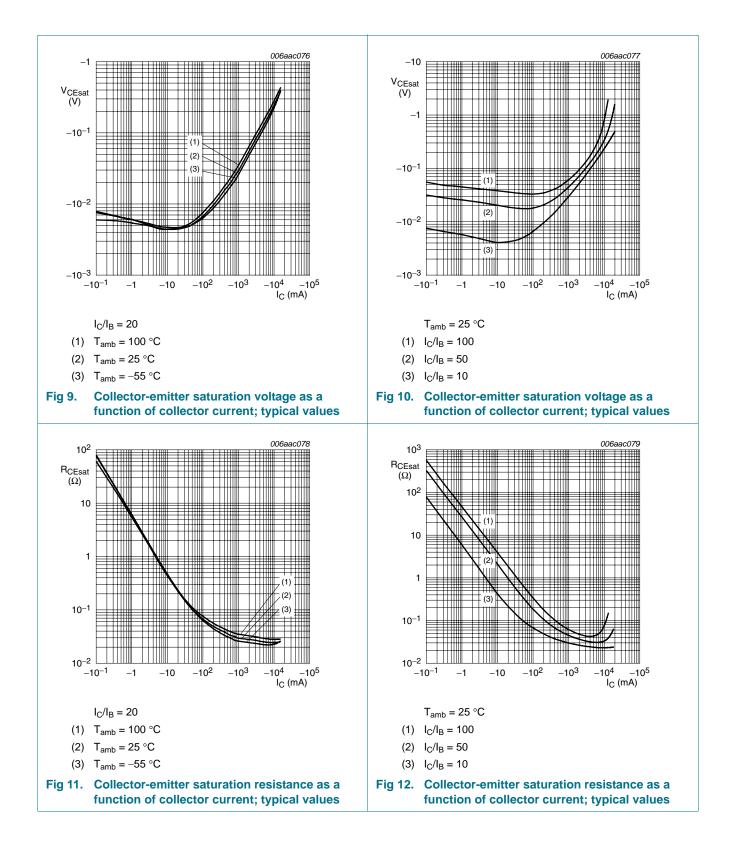
PBSS4021PZ

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor



PBSS4021PZ

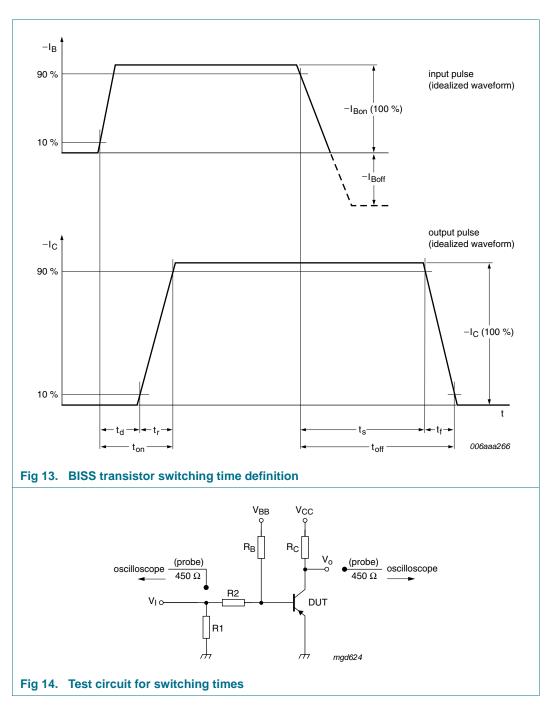
20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor



PBSS4021PZ 1

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

8. Test information

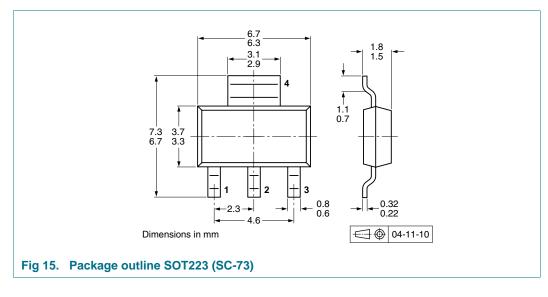


8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

9. Package outline



10. Packing information

Table 8. Packing methods

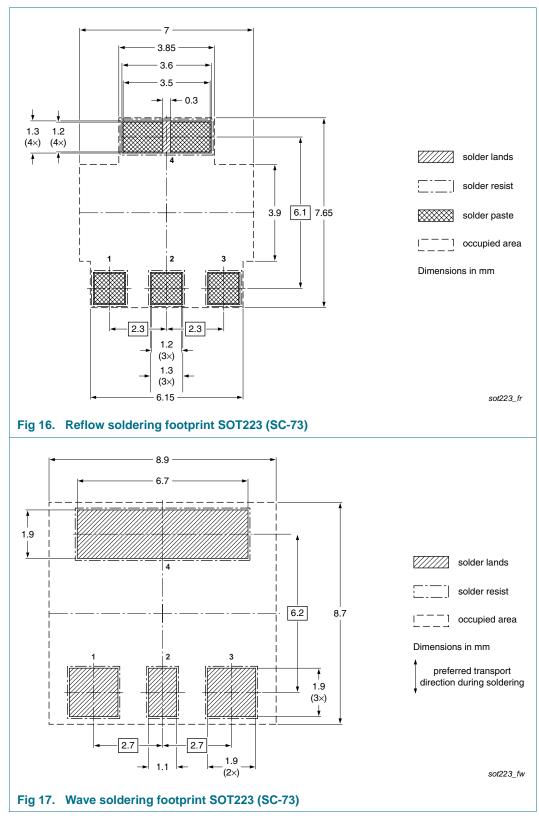
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			1000	4000
PBSS4021PZ	SOT223	8 mm pitch, 12 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

11. Soldering



All information provided in this document is subject to legal disclaimers.

PBSS4021PZ_1

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

12. Revision history

Table 9. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4021PZ_1	20100331	Product data sheet	-	-

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any

representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and

customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

13.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on a weakness or default in the customer application/use or the application/use of customer's third party customer(s) (hereinafter both referred to as "Application"). It is customer's sole responsibility to check whether the Nexperia product is suitable and fit for the Application planned. Customer has to do all necessary testing for the Application in order to avoid a default of the Application and the product. Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale - Nexperia

products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

All information provided in this document is subject to legal disclaimers.

PBSS4021PZ 1

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

14. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

20 V, 6.6 A PNP low V_{CEsat} (BISS) transistor

15. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 4
7	Characteristics 6
8	Test information
8.1	Quality information 9
9	Package outline 10
10	Packing information 10
11	Soldering 11
12	Revision history 12
13	Legal information 13
13.1	Data sheet status 13
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks 13
14	Contact information 14
15	Contents 15

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Nexperia manufacturer:

Other Similar products are found below :

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA 2N2369ADCSM 2N5769 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E US6T6TR NJL0281DG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR MCH6102-TL-E NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13 NTE15